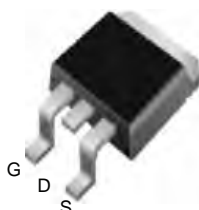


N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
200	0.022 at $V_{GS} = 10$ V	70

D²PAK
(TO-263)



Top View



N-Channel MOSFET

FEATURES

- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- 100 % R_g and UIS tested

APPLICATIONS

- LCD/LED TV
- Consumer Appliances
- Lighting
- AC-DC Power Supply



RoHS*
COMPLIANT

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	200	V
Gate-Source Voltage			V _{GS}	± 20	
Continuous Drain Current	V _{GS} at 10 V	T _C = 25 °C	I _D	70 ^a	A
		T _C = 100 °C		65 ^a	
Pulsed Drain Current			I _{DM}	280	
Single Pulse Avalanche Energy			E _{AS}	165	mJ
Avalanche Current			I _{AR}	68	A
Repetitiive Avalanche Energy			E _{AR}	24	mJ
Maximum Power Dissipation	T _C = 25 °C		P _D	375	W
	T _A = 25 °C ^b			3.1 ^c	
Peak Diode Recovery dV/dt			dV/dt	5.0	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB Mounted, Steady-State)	R_{thJA}	-	35	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.45	

a. Package limited.

b. When Mounted on 1" square PCB (FR-4 material).

c. See SOA curve for voltage derating.

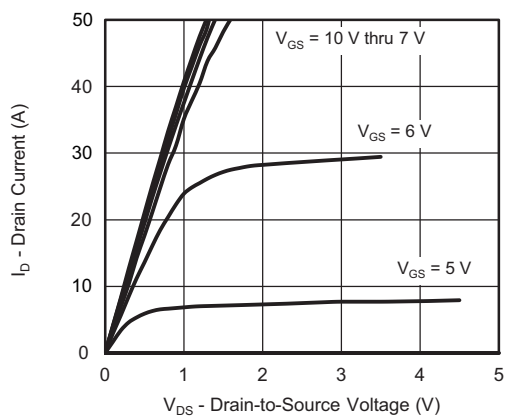
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	200	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2	-	4	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 160 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 160 V, V _{GS} = 0 V, T _J = 125 °C	-	-	100	
		V _{DS} = 160 V, V _{GS} = 0 V, T _J = 175 °C	-	-	2	mA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	25	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A	-	0.022	0.032	Ω
		V _{GS} = 7.5 V, I _D = 25 A	-	0.027	0.039	
Forward Transconductance ^a	g _{fs}	V _{DS} = 20 V, I _D = 30 A	-	15	-	S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz	-	5050	-	pF
Output Capacitance	C _{oss}		-	450	-	
Reverse Transfer Capacitance	C _{rss}		-	90	-	
Total Gate Charge ^c	Q _g	V _{DS} = 100 V, V _{GS} = 10 V, I _D = 30 A	-	90	130	nC
Gate-Source Charge ^c	Q _{gs}		-	25	-	
Gate-Drain Charge ^c	Q _{gd}		-	33	-	
Gate Resistance	R _g	f = 1 MHz	-	3.9	-	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 100 V, R _L = 1.67 Ω I _D ≅ 30 A, V _{GEN} = 10 V, R _g = 1 Ω	-	15	26	ns
Rise Time ^c	t _r		-	25	44	
Turn-Off Delay Time ^c	t _{d(off)}		-	27	54	
Fall Time ^c	t _f		-	9	20	
Drain-Source Body Diode Ratings and Characteristics ^b (T _C = 25 °C)						
Pulsed Current (t = 100 μs)	I _{SM}		-	-	280	A
Forward Voltage ^a	V _{SD}	I _F = 20 A, V _{GS} = 0 V		0.75	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 20 A, d/dt = 100 A/μs	-	88	176	ns
Peak Reverse Recovery Charge	I _{RM(REC)}		-	5	10	A
Reverse Recovery Charge	Q _{rr}			0.22	0.44	μC

Notes

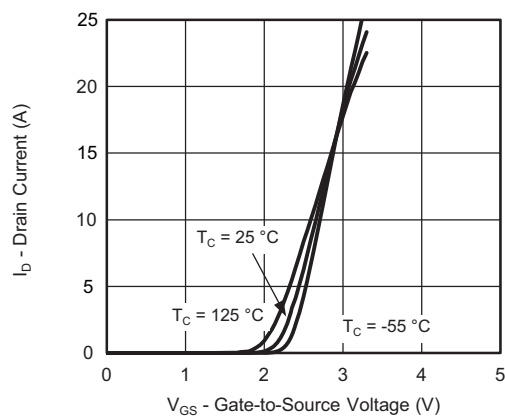
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

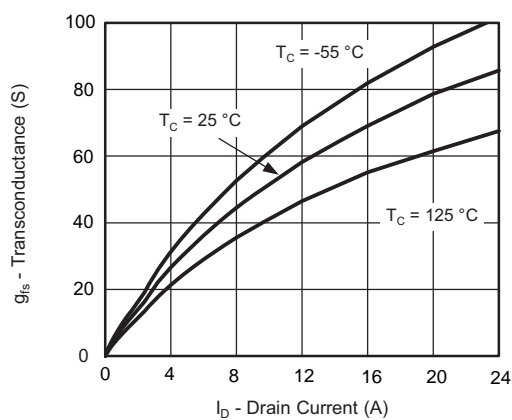
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



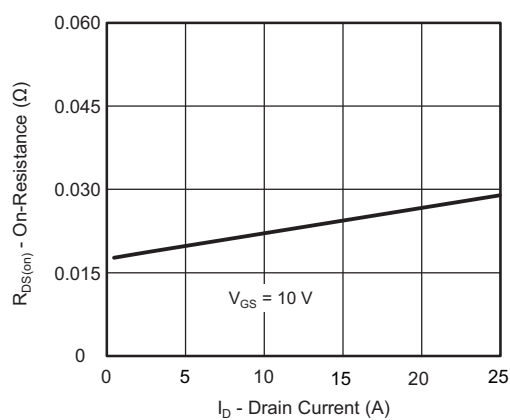
Output Characteristics



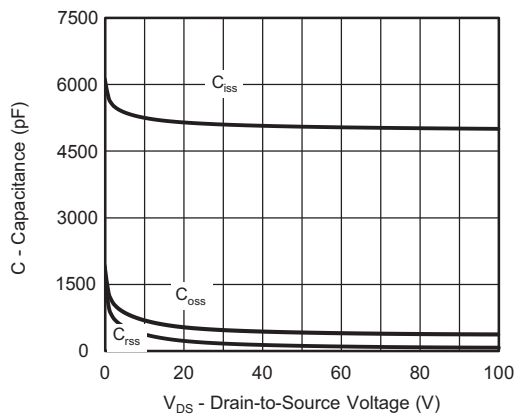
Transfer Characteristics



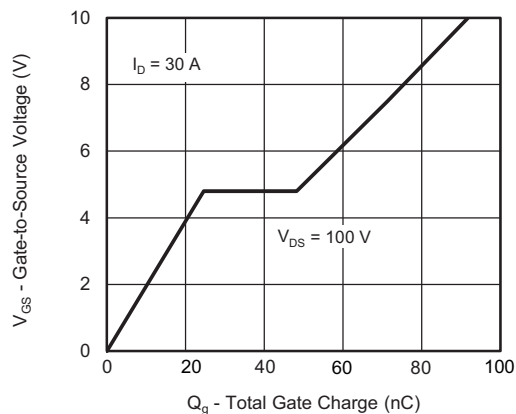
Transconductance



On-Resistance vs. Drain Current

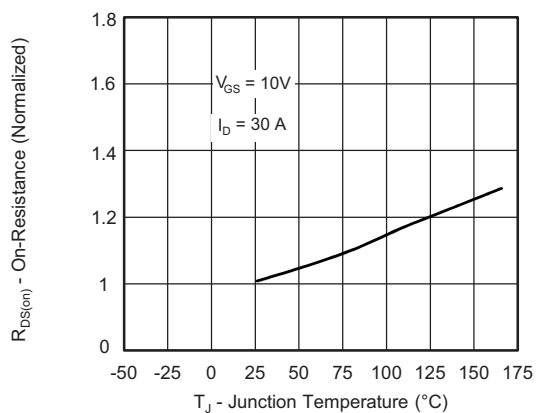


Capacitance

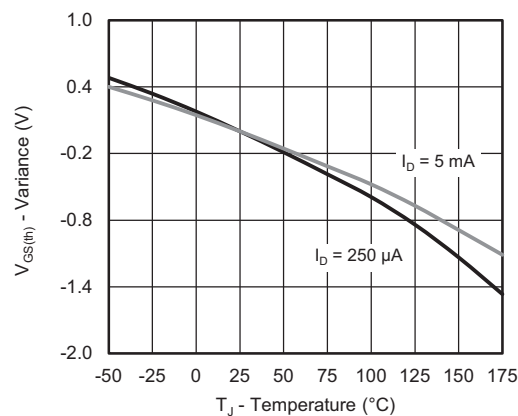


Gate Charge

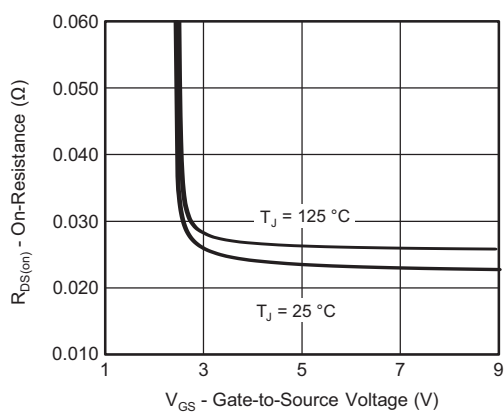
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



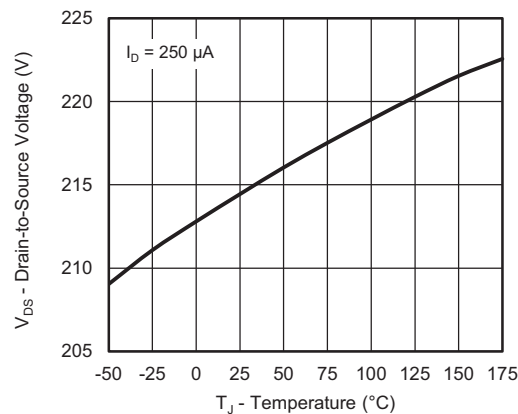
On-Resistance vs. Junction Temperature



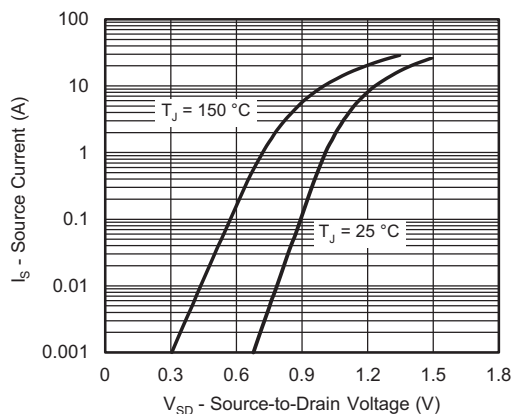
Threshold Voltage



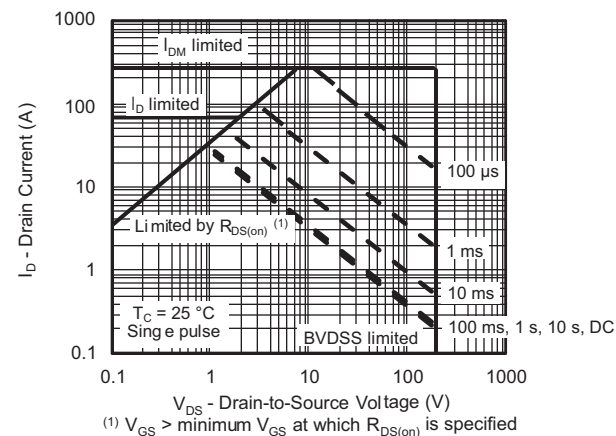
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



Safe Operating Area

(1) $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

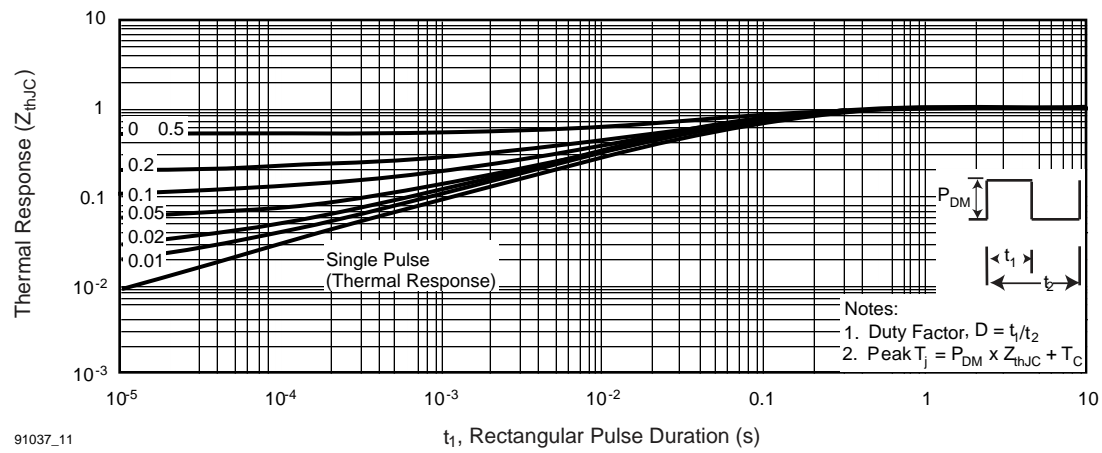


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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